

SMD Schottky Barrier Diode

Comchip
SMD Diode Specialist

CDBU0530

Io = 500 mA

VR = 20 Volts

RoHS Device

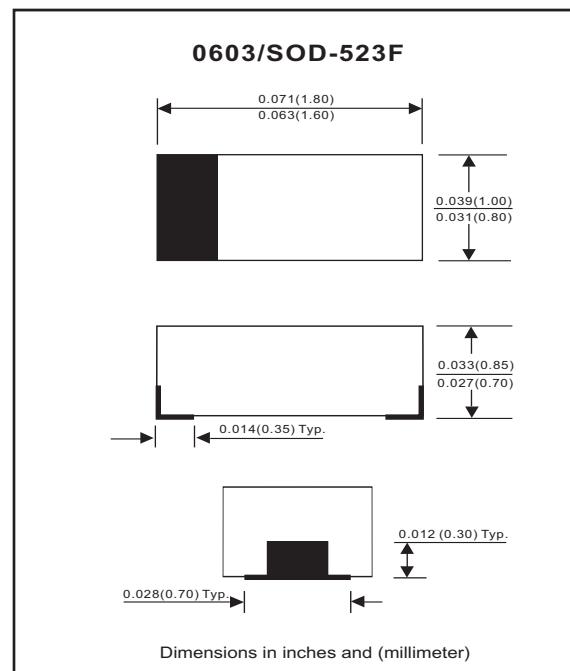


Features

- Low forward voltage.
- Designed for mounting on small surface.
- Extremely thin / leadless package.
- Majority carrier conduction.

Mechanical data

- Case: 0603/SOD-523F standard package, molded plastic.
- Terminals: Gold plated, solderable per MIL-STD-750, method 2026.
- Polarity: Indicated by cathode band.
- Mounting position: Any.
- Weight: 0.003 gram(approx.).



Maximum Rating (at TA=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Peak reverse voltage		V _{RM}			30	V
Reverse voltage		V _R			20	V
Average forward rectified current		I _O			0.5	A
Forward current,surge peak	8.3 ms single half sine-wave superimposed on rate load (JEDEC method)	I _{FSM}			2	A
Storage temperature		T _{TSG}	-40		+125	°C
Junction temperature		T _j			+125	°C

Electrical Characteristics (at TA=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	I _F = 100mA I _F = 500mA	V _F			0.36 0.47	V
Reverse current	V _R = 20V	I _R			100	uA
Capacitance between terminals	f = 1 MHz, and 0 VDC reverse voltage	C _T		100		pF

RATING AND CHARACTERISTIC CURVES (CDBU0530)

Fig. 1 - Forward characteristics

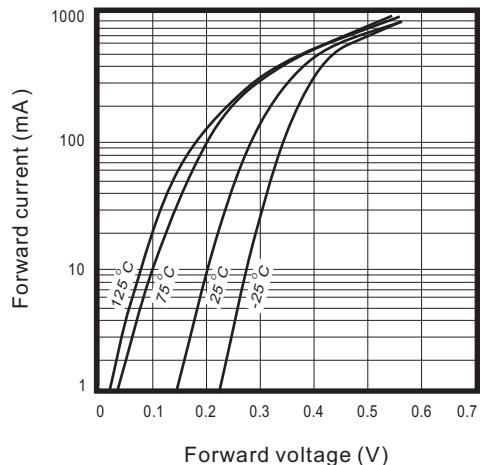


Fig. 2 - Reverse characteristics

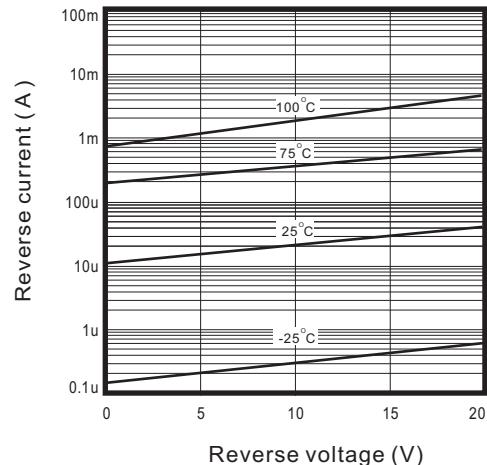


Fig. 3 - Capacitance between terminals characteristics

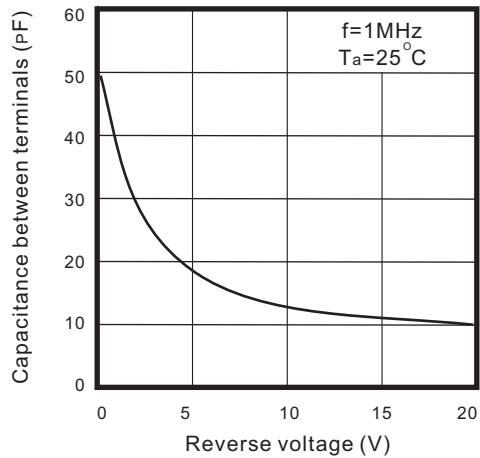


Fig.4 - Current derating curve

